FIG. 8 is two cross sections indicating the shapes before manufacturing and after manufacturing the oxide film holes on the wafer member to be treated using the present invention,

B2

Page 14, the fifth full paragraph, lines 20-21, replace the paragraph as follows:

FIG. 9 is a cross section of another dry etching apparatus using the present invention,

B3

Page 14, the sixth full paragraph, lines 22-23, replace the paragraph as follows:

FIG. 10 is a cross section of another dry etching apparatus using the present invention,

B4

Page 14, between lines 23-24, insert following paragraph:

FIG. 11 is a cross section of another dry etching apparatus using the present invention,

B5

Page 14, the seventh full paragraph, lines 24-26, replace the paragraph as follows:

FIG. 12 is two cross sections indicating the shapes before manufacturing and after manufacturing on the member to be treated using in the present invention,

B6

Pages 14 and 15, the paragraph bridging page 14, line 27, through page 15, line 4, replace the paragraph as follows:

B7 FIG. 13 is an illustration indicating the dependency of the injection ratio of $CF_2/(F + O)$, and the injection ratio of CF_2/ions of the member to be treated on the C_4F_8 gas flow rate using for explanation of the present invention, and

Page 15, the first full paragraph, lines 5-9, replace the paragraph as follows:

B8 FIG. 14 is an illustration indicating the dependency of the selection ratio at a shoulder portion of the silicone nitride film and the manufacturing shape (taper angle) on the C_4F_8 gas flow rate using for explanation of the present invention.

Pages 26 and 27, the paragraph bridging page 26, line 17, through page 27, line 12, replace the paragraph as follows:

B9 As the member to be treated 6, eight inches silicone wafer having the structure indicted in FIG. 8 formed on its surface is transferred from an adjacent transfer chamber (not shown in the figure) via a gate valve 16. The wafer 88 before etching is composed of a silicone wafer 87 having a gate oxide film 86 of 4 nm thick formed thereon, and gate electrodes 85

B9 cont

of 300 nm thick and 80 nm wide composed of polycrystalline Si and W formed on a part of the surface of the gate oxide film. Silicone nitride film 84 of 200 nm thick is formed on the upper surface of the gate electrode, and silicone nitride film 84 of 60 nm thick is formed on the side surface of the gate electrode and the upper surface of the gate oxide film so as to cover the gate electrode 85. An oxide film 83 (SOG and CVD oxide film) of 1600 nm thick (at the most thick portion) is formed on the upper surface of the silicone nitride film. Above the film, a reflection preventing film 82 of 80 nm thick and a resist mask 81, whereon a hole pattern of 130 nm in diameter is exposed and developed, of 500 nm thick are formed. The width of the oxide film 83 existing between the gate electrode is approximately 60 nm.

Pages 30 and 31, the paragraph bridging page 30, line 12, through page 31, line 5, replace the paragraph as follows:

B10

Next, the oxide film etching was performed on a self-align contact (SAC) structure indicated in FIG. 8. FIG. 8 on the left side indicates a cross section of the wafer before etching, and FIG. 8 on the right side indicates a cross section of the wafer after etching. The result is indicated as the shape 89 after etching. After starting the etching, the silicone nitride film begins to be appeared after